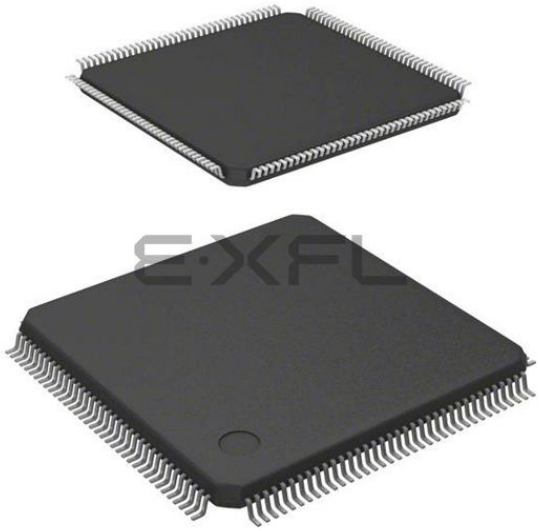

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	36MHz
Connectivity	CANbus, I²C, SPI, UART/USART
Peripherals	DMA, POR, PWM, WDT
Number of I/O	112
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	4.5V ~ 5.5V
Data Converters	A/D 16x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str730fz2t6

clock/calendar/alarm function. When the STR73xF is in LPWFI mode the RTC keeps running, powered by the low power voltage regulator.

UARTs

The 4 UARTs allow full duplex, asynchronous, communications with external devices with independently programmable TX and RX baud rates up to 625 Kbaud.

Buffered serial peripheral interfaces (BSPI)

Each of the three BSPIs allow full duplex, synchronous communications with external devices, master or slave communication at up to 6 Mb/s in master mode and up to 4.5 Mb/s in slave mode (@36 MHz system clock).

I^2C interfaces

The two I^2C Interfaces provide multi-master and slave functions, support normal and fast I^2C mode (400 kHz) and 7 or 10-bit addressing modes.

A/D converter

The 10-bit analog to digital converter, converts up to 16 channels in single-shot or continuous conversion modes (12 channels in 100-pin devices). The minimum conversion time is 3 µs.

Watchdog

The 16-bit watchdog timer protects the application against hardware or software failures and ensures recovery by generating a reset.

I/O ports

Up to 112 I/O ports (72 in 100-pin devices) are programmable as general purpose input/output or alternate function.

External interrupts and wake-up lines

16 external interrupts lines are available for application use. In addition, up to 32 external Wake-up lines (18 in 100-pin devices) can be used as general purpose interrupts or to wake-up the application from STOP mode.

3 Block diagram

Figure 1. STR730F/STR735F block diagram

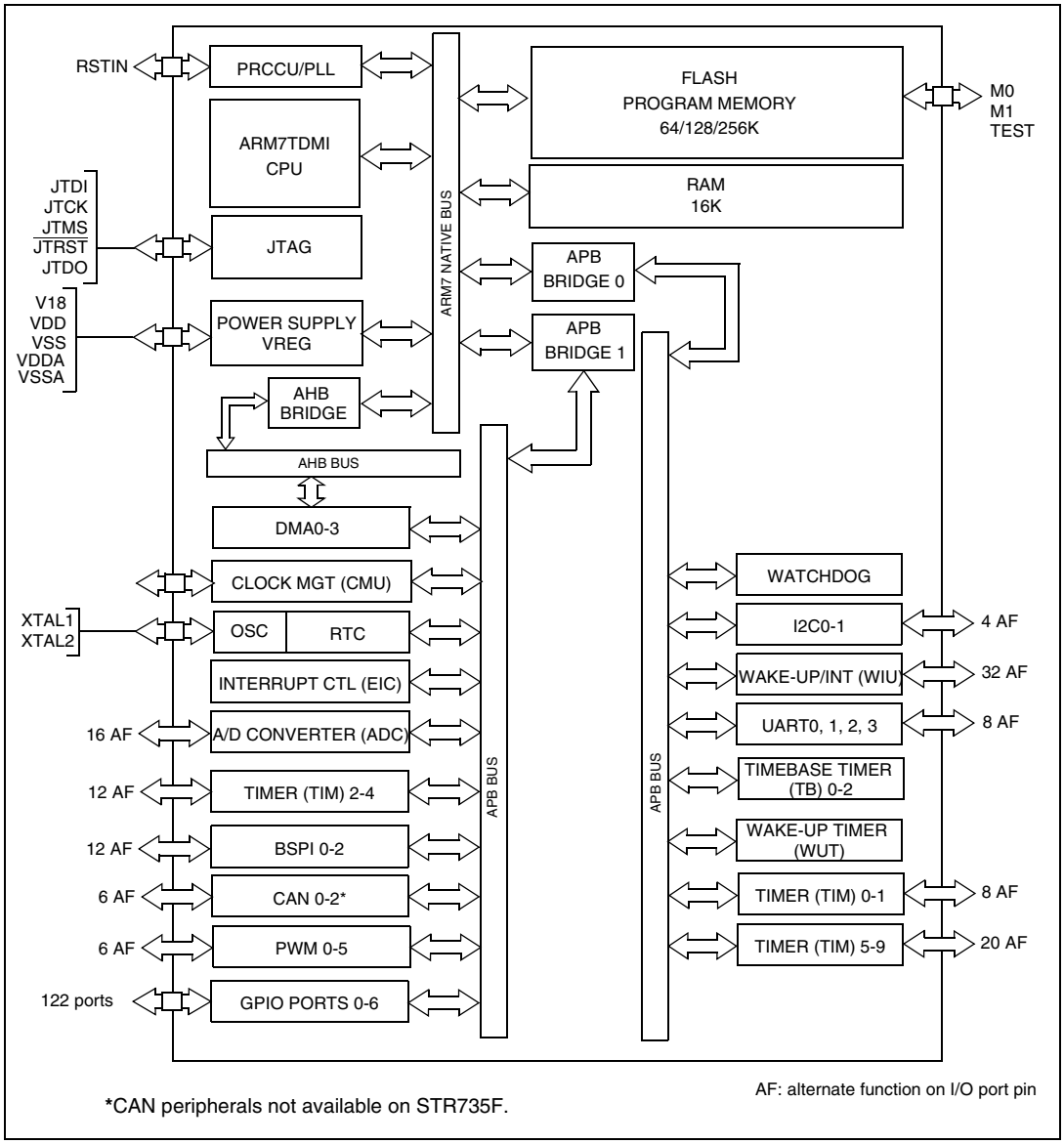
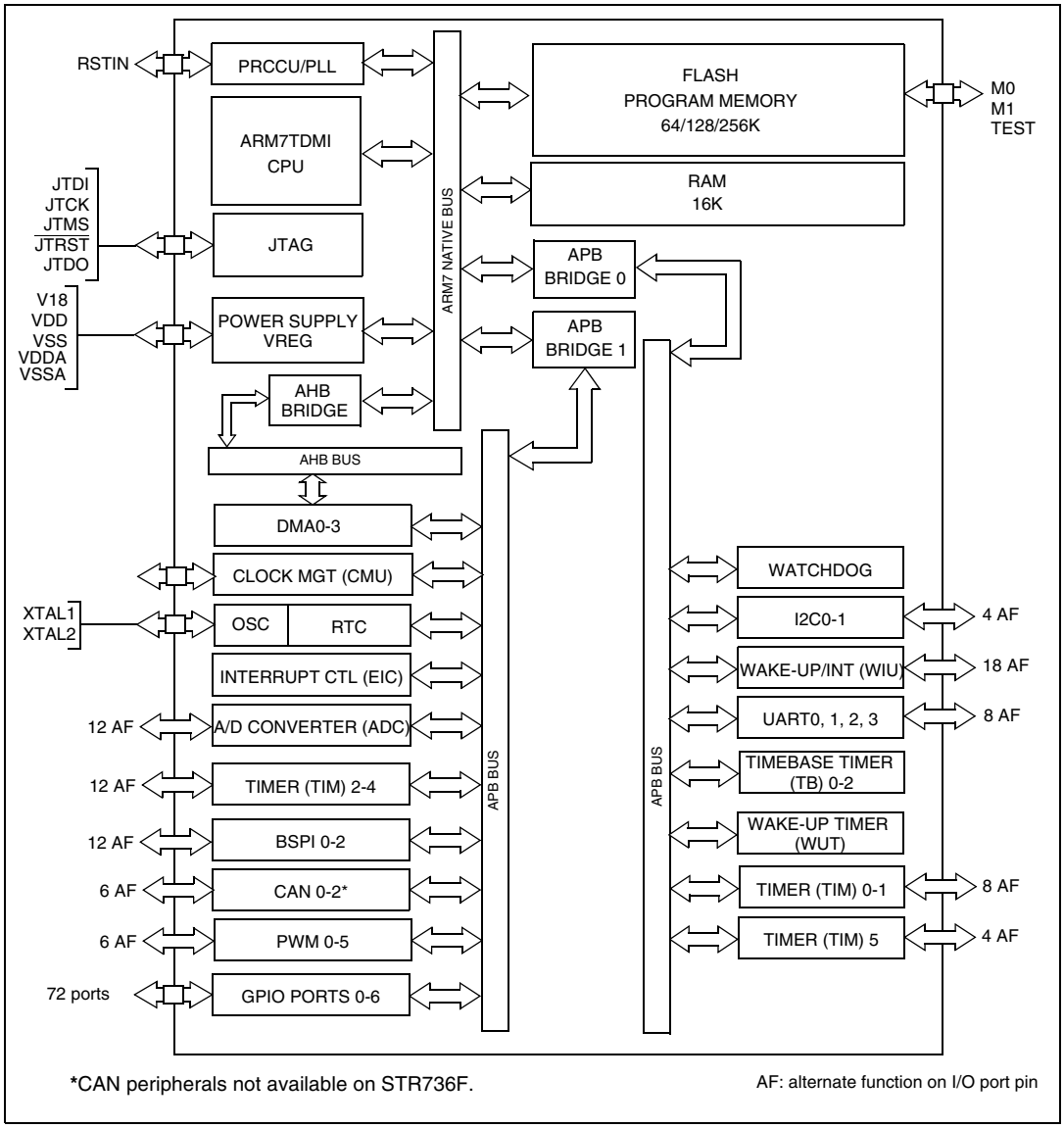


Figure 2. STR731F/STR736 block diagram



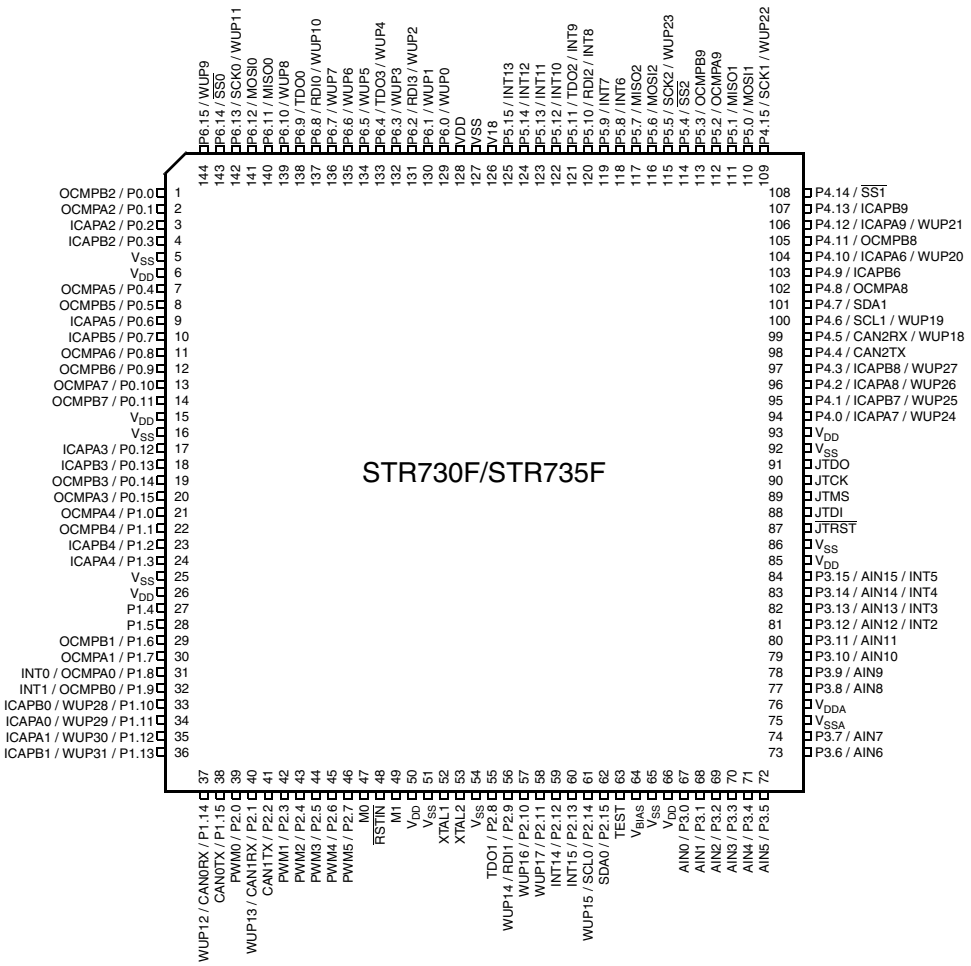
*CAN peripherals not available on STR736F.

AF: alternate function on I/O port pin

3.2 Pin description

3.2.1 STR730F/STR735F (TQFP144)

Figure 3. STR730F/STR735F pin configuration (top view)



Note: CAN alternate functions not available on STR735F.

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function	
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP			
50	J5	36	V_{DD}	S							Supply voltage (5 V)		
51	M6	37	V_{SS}	S							Ground		
52	M7	38	XTAL1	I							Oscillator amplifier circuit input and internal clock generator input.		
53	H5	39	XTAL2	O							Oscillator amplifier circuit output.		
54	L6	40	V_{SS}	S							Ground		
55	K6	41	P2.8/TDO1/CAN2RX	I/O	T_T			2mA	X	X	Port 2.8	UART1: transmit data output	CAN2: receive data input (TQFP100 only)
56	J6	42	P2.9/RDI1/CAN2TX	I/O	T_T		WUP14	2mA	X	X	Port 2.9	UART1: receive data input	CAN2: transmit data output (TQFP100 only)
57	H6		P2.10	I/O	T_T		WUP16	2mA	X	X	Port 2.10		
58	G6		P2.11	I/O	T_T		WUP17	2mA	X	X	Port 2.11		
59	L7		P2.12	I/O	T_T		INT14	2mA	X	X	Port 2.12		
60	K7		P2.13	I/O	T_T		INT15	2mA	X	X	Port 2.13		
61	J7	43	P2.14/SCL0	I/O	T_T		WUP15	2mA	X	X	Port 2.14	I2C0: serial clock	
62	H7	44	P2.15/SDA0	I/O	T_T			2mA	X	X	Port 2.15	I2C0: serial data	
63	M8	45	Test	I		pd					Reserved pin. Must be tied to ground		
64	L8	46	V_{BIAS}	S							Internal RC oscillator bias. A 1.3 MΩ external resistor has to be connected to this pin when a 32 kHZ RC oscillator frequency is used.		
65	M10	47	V_{SS}	S							Ground		
66	M11	48	V_{DD}	S							Supply voltage (5 V)		
67	K8		P3.0/AIN0	I/O	T_T			2mA	X	X	Port 3.0	ADC: analog input 0	
68	J8		P3.1/AIN1	I/O	T_T			2mA	X	X	Port 3.1	ADC: analog input 1	
69	M9		P3.2/AIN2	I/O	T_T			2mA	X	X	Port 3.2	ADC: analog input 2	
70	L9		P3.3/AIN3	I/O	T_T			2mA	X	X	Port 3.3	ADC: analog input 3	
71	K9	49	P3.4/AIN4	I/O	T_T			2mA	X	X	Port 3.4	ADC: analog input 4 (AIN0 in TQFP100)	
72	L10	50	P3.5/AIN5	I/O	T_T			2mA	X	X	Port 3.5	ADC: Analog input 5 (AIN1 in TQFP100)	

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function	
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP			
97	F9		P4.3/ICAPB8	I/O	T_T		WUP27	2mA	X	X	Port 4.3	TIM8: input capture B input	
98	F8		P4.4/CAN2TX	I/O	T_T			2mA	X	X	Port 4.4	CAN2: transmit data output	
99	E12		P4.5/CAN2RX	I/O	T_T		WUP18	2mA	X	X	Port 4.5	CAN2: receive data input	
100	E11	72	P4.6/SCL1	I/O	T_T		WUP19	2mA	X	X	Port 4.6	I2C1: serial clock	
101	C12	73	P4.7/SDA1	I/O	T_T			2mA	X	X	Port 4.7	I2C1: serial data	
102	B12		P4.8/OCMPA8	I/O	T_T			2mA	X	X	Port 4.8	TIM8: output compare A output	
103	E10		P4.9/ICAPB6	I/O	T_T			2mA	X	X	Port 4.9	TIM6: input capture B input	
104	E9	74	P4.10/ICAPA6/ICAPB5	I/O	T_T		WUP20	2mA	X	X	Port 4.10	TIM6: input capture A input (144-pin pkg only)	TIM5: input capture B input (TQFP100 only)
105	D12		P4.11/OCMPB8	I/O	T_T			2mA	X	X	Port 4.11	TIM8: output compare B output	
106	D11		P4.12/ICAPA9	I/O	T_T		WUP21	2mA	X	X	Port 4.12	TIM9: input capture A input	
107	D10		P4.13/ICAPB9	I/O	T_T			2mA	X	X	Port 4.13	TIM9: input capture B input	
108	C11	75	P4.14/$\overline{SS}$1	I/O	T_T			2mA	X	X	Port 4.14	BSPI1: slave select	
109	B11	76	P4.15/SCK1	I/O	T_T		WUP22	2mA	X	X	Port 4.15	BSPI1: serial clock	
110	B10	77	P5.0/MOSI1	I/O	T_T			2mA	X	X	Port 5.0	BSPI1: master output/slave input	
111	C10	78	P5.1/MISO1	I/O	T_T			2mA	X	X	Port 5.1	BSPI1: master input/Slave output	
112	A9		P5.2/OCMPA9	I/O	T_T			2mA	X	X	Port 5.2	TIM9: output compare A output	
113	B9		P5.3/OCMPB9	I/O	T_T			2mA	X	X	Port 5.3	TIM9: output compare B output	
114	C9	79	P5.4/$\overline{SS}$2/PWM3	I/O	T_T			2mA	X	X	Port 5.4	BSPI2: slave select	PWM3: PWM output (TQFP100 only)
115	D9	80	P5.5/SCK2	I/O	T_T		WUP23	2mA	X	X	Port 5.5	BSPI2: serial clock	
116	A11	81	P5.6/MOSI2	I/O	T_T			2mA	X	X	Port 5.6	BSPI2: master output/slave input	
117	A10	82	P5.7/MISO2	I/O	T_T			2mA	X	X	Port 5.7	BSPI2: master input/slave output	
118	A8	83	P5.8/PWM4	I/O	T_T		INT6	2mA	X	X	Port 5.8	PWM4: PWM output (TQFP100 only)	

Table 4. STR73xF pin description

Pin n°			Pin name	Type	Input			Output			Main function (after reset)	Alternate function
TQFP144	LFBGA144	TQFP100			Input Level	pu/pd	interrupt	Capability	OD	PP		
119	B8	84	P5.9/PWM5	I/O	T_T		INT7	2mA	X	X	Port 5.9	PWM5: PWM output (TQFP100 only)
120	C8	85	P5.10/RDI2	I/O	T_T		INT8	2mA	X	X	Port 5.10	UART2: receive data input
121	A12	86	P5.11/TDO2	I/O	T_T		INT9	2mA	X	X	Port 5.11	UART2: transmit data output
122	D8	87	P5.12	I/O	T_T		INT10	2mA	X	X	Port 5.12	
123	E8		P5.13	I/O	T_T		INT11	2mA	X	X	Port 5.13	
124	B7		P5.14	I/O	T_T		INT12	2mA	X	X	Port 5.14	
125	A7		P5.15	I/O	T_T		INT13	2mA	X	X	Port 5.15	
126	A6	88	V_{18}	S								1.8 V decoupling pin: a decoupling capacitor (recommended value: 100 nF) must be connected between this pin and nearest VSS pin.
127	C7	89	V_{SS}	S								Ground
128	D7	90	V_{DD}	S								Supply voltage (5 V)
129	E7	91	P6.0	I/O	T_T		WUP0	8mA	X	X	Port 6.0	
130	F7		P6.1	I/O	T_T		WUP1	2mA	X	X	Port 6.1	
131	B6	92	P6.2/RDI3	I/O	T_T		WUP2	2mA	X	X	Port 6.2	UART3: receive data input
132	C6		P6.3	I/O	T_T		WUP3	2mA	X	X	Port 6.3	
133	D6	93	P6.4/TDO3	I/O	T_T		WUP4	2mA	X	X	Port 6.4	UART3: transmit data output
134	E6		P6.5	I/O	T_T		WUP5	2mA	X	X	Port 6.5	
135	A5	94	P6.6	I/O	T_T		WUP6	2mA	X	X	Port 6.6	
136	B5		P6.7	I/O	T_T		WUP7	2mA	X	X	Port 6.7	
137	C5	95	P6.8/RDI0	I/O	T_T		WUP10	2mA	X	X	Port 6.8	UART0: receive data input
138	A3	96	P6.9/TDO0	I/O	T_T			2mA	X	X	Port 6.9	UART0: transmit data output
139	A2		P6.10	I/O	T_T		WUP8	2mA	X	X	Port 6.10	
140	D5	97	P6.11/MISO0	I/O	T_T			2mA	X	X	Port 6.11	BSPI0: master input/slave output
141	A4	98	P6.12/MOSI0	I/O	T_T			2mA	X	X	Port 6.12	BSPI0: master output/slave input
142	B4	99	P6.13/SCK0	I/O	T_T		WUP11	2mA	X	X	Port 6.13	BSPI0: serial clock
143	C4	100	P6.14/$\overline{SS}$0	I/O	T_T			2mA	X	X	Port 6.14	BSPI0: slave select
144	B3		P6.15	I/O	T_T		WUP9	2mA	X	X	Port 6.15	

4 Electrical parameters

4.1 Parameter conditions

Unless otherwise specified, all voltages are referred to V_{SS}.

4.1.1 Minimum and maximum values

Unless otherwise specified the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A=25° C and T_A=T_{Amax} (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean±3Σ).

4.1.2 Typical values

Unless otherwise specified, typical data are based on T_A=25° C and V_{DD}=5 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean±2Σ).

4.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

4.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 6*.

4.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 7*.

Figure 6. Pin loading conditions

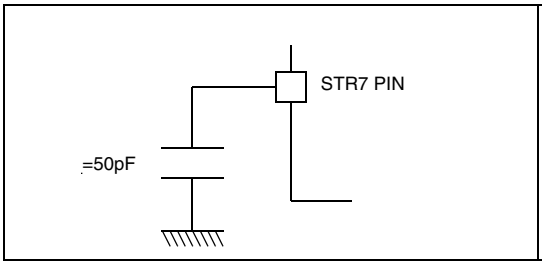


Figure 7. Pin input voltage

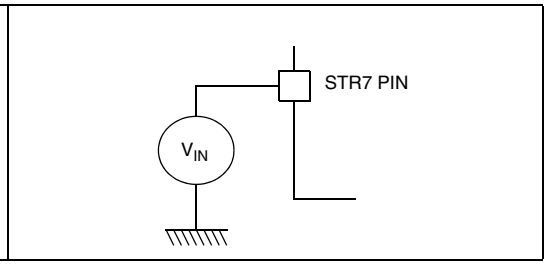


Table 7. Thermal characteristics

Symbol	Ratings	Value	Unit
T_{STG}	Storage temperature range	-55 to +150	°C
T_J	Maximum junction temperature (see *Section 5.2: Thermal characteristics on page 48*)		

4.3 Operating conditions

Subject to general operating conditions for V_{DD}, and T_A.

Table 8. General operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
f_{MCLK}	Internal CPU and system clock frequency	Accessing SRAM or Flash (zero wait state Flash access up to 36 MHz)	0	36	MHz
V_{DD}	Standard Operating Voltage		4.5	5.5	V
V_{DDA}	Operating analog reference voltage with respect to ground		4.5	V_{DD}+0.1	V
T_A	Ambient temperature range	6 partnumber suffix 7 partnumber suffix	-40 -40	85 105	°C

Table 9. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{VDD}	V_{DD} rise time rate	Subject to general operating conditions for T_A.	-	20	-	ms/V

On-chip peripherals

Table 13. Peripheral current consumption at T_A= 25°C

Symbol	Parameter	Conditions	Typ	Unit
$I_{DD(RC)}$	RC (backup oscillator) supply current	High frequency	120	µA
		Low frequency	60	µA
$I_{DD(TIM)}$	TIM timer supply current [1]	f_{MCLK}=36 MHz	350	µA
$I_{DD(BSPI)}$	BSPI supply current [1]		1.1	mA
$I_{DD(UART)}$	UART supply current [1]		850	µA
$I_{DD(I2C)}$	I2C supply current [1]		430	µA
$I_{DD(ADC)}$	ADC supply current when converting [2]		5	mA
$I_{DD(EIC)}$	EIC supply current		2.88	mA
$I_{DD(CAN)}$	CAN supply current [1]		2.95	mA
$I_{DD(GPIO)}$	GPIO supply current		150	µA
$I_{DD(TB)}$	TB supply current		250	µA
$I_{DD(PWM)}$	PWM supply current		240	µA
$I_{DD(RTC)}$	RTC supply current		370	µA
$I_{DD(DMA)}$	DMA supply current		2.5	mA
$I_{DD(ARB)}$	Native arbiter supply current		180	µA
$I_{DD(AHB)}$	AHB arbiter supply current		570	µA
$I_{DD(WUT)}$	WUT supply current		300	µA
$I_{DD(WIU)}$	WIU supply current		460	µA

1. Data based on a differential I_{DD} measurement between the on-chip peripheral when kept under reset, not clocked and the on-chip peripheral when clocked and not kept under reset. This measurement does not include the pad toggling consumption.
2. Data based on a differential I_{DD} measurement between reset configuration and continuous A/D conversions.

RC/backup oscillator characteristics

V_{DD} = 5V ± 10%, T_A = -40°C to T_{Amax}, unless otherwise specified.

Table 15. RC oscillator characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
f_{RC}	RC frequency	High frequency mode [1]		2.35		MHz
		Low frequency mode[1]		29		kHz
f_{RCHF}	RC high frequency	CMU_RCCTL = 0x0	3			MHz
		CMU_RCCTL = 0xF			2.3	MHz
f_{RCLF}	RC low frequency	CMU_RCCTL = 0x0	35			kHz
		CMU_RCCTL = 0xF			30	kHz
f_{RCHFS}[2]	RC high frequency stability	Fixed CMU_RCCTL			10	%
f_{RCLFS}[2]	RC low frequency stability	Fixed CMU_RCCTL			23	%
t_{RCSTUP}	RC start-up time	Stable V_{DD}, f_{RC} = 2.35 MHz, T_A = 25°C		2.35		µs

1) CMU_RCCTL = 0x8

2) RC frequency shift versus average value (%)

PLL electrical characteristics

V_{DD} = 5 V ± 10%, T_A = -40° C to T_{Amax}, unless otherwise specified

Table 16. PLL characteristics

Symbol	Parameter	Conditions	Value			Unit
			Min	Typ	Max	
f_{PLLIN} (1)	PLL reference clock	FREF_RANGE = '0' FREF_RANGE = '1'	1.5 3.0		3.0 5.0	MHz
f_{PLLOUT}	PLL output clock	MX = "00" MX = "01" MX = "10" MX = "11"	20 x f_{PLLIN} 12 x f_{PLLIN} 28 x f_{PLLIN} 16 x f_{PLLIN}			MHz
f_{MCLK}	System clock	DX = 1..7	f_{PLLOUT}/DX		36	MHz
f_{FREE} (2)	PLL free running frequency	FREF_RANGE = '0', MX0 = '1' FREF_RANGE = '0', MX0 = '0' FREF_RANGE = '1', MX0 = '1' FREF_RANGE = '1', MX0 = '0'		120 240 240 480		kHz
t_{LOCK} (3)	PLL lock time	Stable oscillator (f_{PLLIN} = 4 MHz), stable V_{DD}		100	300	µs
Δt_{PKJIT}	PLL jitter (pk to pk)	f_{PLLIN} = 4 MHz (pulse generator)			1.5	ns

1. f_{PLLIN} is obtained from f_{OSC} directly or through an optional divider by 2.
2. Typical data are based on T_A=25°C, V_{DD}=5V
3. Max value is guaranteed by characterization, not tested in production.

Table 17. Low-power mode wake-up timing

Symbol	Parameter	Conditions	Typ	Unit
t_{WUHALT}	Wake-up from HALT mode		200	µs
t_{WUSTOP}	Wake-up from STOP mode	RC high frequency in STOP mode	180	µs
		RC low frequency in STOP mode	234	µs
$t_{WULPWFI}$ 1)	Wake-up from LPWFI mode	Main voltage regulator on RC oscillator off f_{OSC} = 4 MHz, f_{MCLK}= f_{OSC}/16 RAM or FLASH execution	27	µs
		Main voltage regulator on RC oscillator = high frequency Flash execution	46	µs
		Main voltage regulator on RC oscillator = low frequency Flash execution	3.6	ms

1. Flash memory programmed to enter Power Down mode during LPWFI.

4.3.3 Memory characteristics

Flash memory

Table 18. Flash memory characteristics

Symbol	Parameter	Test Conditions	Value			Unit
			Min	Typ	Max[1)]	
t_{WP}	Word program (32-bit)			35	80	µs
t_{DWP}	Double word program(64-bit)			64	150	µs
t_{BP64}	Bank program (64 K)	Double word program		0.5	1.25	s
t_{BP128}	Bank program (128 K)	Double word program		1	2.5	s
t_{BP256}	Bank program (256 K)	Double word program		2	4.9	s
t_{SE8}	Sector erase (8 K)	Not preprogrammed Preprogrammed [2)]		0.6 0.5	0.9 0.8	s
t_{SE32}	Sector erase (32 K)	Not preprogrammed Preprogrammed[2)]		1.1 0.8	2 1.8	s
t_{SE64}	Sector erase (64 K)	Not preprogrammed preprogrammed [2)]		1.7 1.3	3.7 3.3	s
t_{RPD}[3)]	Recovery from power-down				20	µs
t_{PSL}[3)]	Program suspend latency				10	µs
t_{ESL}[3)]	Erase suspend latency				30	µs
t_{ESR}[3)]	Erase suspend rate	Min. time from erase resume to next erase suspend		20	20	ms
t_{SP}[3)]	Set protection			40	170	µs
t_{FPW}[3)]	First word program			1		ms
N_{END}	Endurance		10			kcycles
t_{RET}	Data retention	T_A = 85° C	20			Years

1. T_A = -45° C after 0 cycles, Guaranteed by characterization, not tested in production.
2. All bits programmed to 0.
3. Guaranteed by design, not tested in production.

4.3.4 EMC characteristics

Susceptibility tests are performed on a sample basis during product characterization.

Functional EMS (electromagnetic susceptibility)

Based on a simple running application on the product (toggling 2 LEDs through I/O ports), the product is stressed by two electromagnetic events until a failure occurs (indicated by the LEDs).

- **ESD**: Electrostatic discharge (positive and negative) is applied on all pins of the device until a functional disturbance occurs. This test conforms with the IEC 1000-4-2 standard.
- **FTB**: A burst of fast transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test conforms with the IEC 1000-4-4 standard.

A device reset allows normal operations to be resumed. The test results are given in the table below based on the EMS levels and classes defined in application note AN1709.

Designing hardened software to avoid noise problems

EMC characterization and optimization are performed at component level with a typical application environment and simplified MCU software. It should be noted that good EMC performance is highly dependent on the user application and the software in particular.

Therefore it is recommended that the user applies EMC software optimization and prequalification tests in relation with the EMC level requested for his application.

Software recommendations:

The software flowchart must include the management of runaway conditions such as:

- Corrupted program counter
- Unexpected reset
- Critical data corruption (control registers...)

Prequalification trials:

Most of the common failures (unexpected reset and program counter corruption) can be reproduced by manually forcing a low state on the RESET pin or the oscillator pins for 1 second.

To complete these trials, ESD stress can be applied directly on the device, over the range of specification values. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring (see application note AN1015).

Table 19. EMS data

Symbol	Parameter	Conditions	Level/ Class
V_{FESD}	Voltage limits to be applied on any I/O pin to induce a functional disturbance	V_{DD}=5 V, T_A=+25° C, f_{MCLK}=36 MHz conforms to IEC 1000-4-2	4A
V_{EFTB}	Fast transient voltage burst limits to be applied through 100 pF on V_{DD} and V_{SS} pins to induce a functional disturbance	V_{DD}=5 V, T_A=+25° C, f_{MCLK}=36 MHz conforms to IEC 1000-4-4	4A

4.3.5 I/O port pin characteristics

General characteristics

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 23. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage [1]	TTL ports			0.8	V
V_{IH}	Input high level voltage [1]		2.0			
$I_{INJ(PIN)}$	Injected current on any I/O pin				±10	mA
$\Sigma I_{INJ(PIN)}$ [2]	Total injected current (sum of all I/O and control pins)				±75	mA
I_{lkg}	Input leakage current [3]	$V_{SS} \leq V_{IN} \leq V_{DD}$			±1	µA
I_S	Static current consumption [4]	Floating input mode		200		µA
R_{PU}	Weak pull-up equivalent resistor[5]	$V_{IN}=V_{SS}$	55	120	220	kΩ
R_{PD}	Weak pull-down equivalent resistor[5]	$V_{IN}=V_{DD}$	55	120	220	kΩ
C_{IO}	I/O pin capacitance			5		pF

1. Data based on characterization results, not tested in production.
2. When the current limitation is not possible, the V_{IN} absolute maximum rating must be respected, otherwise refer to $I_{INJ(PIN)}$ specification. A positive injection is induced by $V_{IN}>V_{33}$ while a negative injection is induced by $V_{IN}<V_{SS}$. Refer to *Section 4.2 on page 22* for more details.
3. Leakage could be higher than max. if negative current is injected on adjacent pins.
4. Configuration not recommended, all unused pins must be kept at a fixed voltage: using the output mode of the I/O for example or an external pull-up or pull-down resistor. Data based on design simulation and/or technology characteristics, not tested in production.
6. The R_{PU} pull-up and R_{PD} pull-down equivalent resistor are based on a resistive transistor (corresponding I_{PU} and I_{PD} current characteristics described in *Figure 19*).

Output driving current

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified.

Table 24. Output driving current

I/O Type	Symbol	Parameter	Conditions	Min	Max	Unit
Standard	V_{OL} 1)	Output low level voltage for an I/O pin when 8 pins are sunk at same time	I_{IO}=+2 mA		0.4	V
	V_{OH} 2)	Output high level voltage for an I/O pin when 4 pins are sourced at same time	I_{IO}=-2 mA	V_{DD}-0.8		
Med. Current (JTDO)	V_{OL} 1)	Output low level voltage for an I/O pin	I_{IO}=+6 mA		0.4	
	V_{OH} 2)	Output high level voltage for an I/O pin	I_{IO}=-6 mA	V_{DD}-0.8		
High Current P6.0	V_{OL} 1)	Output low level voltage for an I/O pin	I_{IO}=+8 mA		0.4	
	V_{OH} 2)	Output high level voltage for an I/O pin	I_{IO}=-8 mA	V_{DD}-0.8		

1. The I_{IO} current sunk must always respect the absolute maximum rating specified in *Table 6* and the sum of I_{IO} (I/O ports and control pins) must not exceed I_{VSS}.
2. The I_{IO} current sourced must always respect the absolute maximum rating specified in *Table 6* and the sum of I_{IO} (I/O ports and control pins) must not exceed IV_{DD}.

Figure 13. V_{OH} standard ports vs I_{OH} @ V_{DD} 5V T_A -45° C

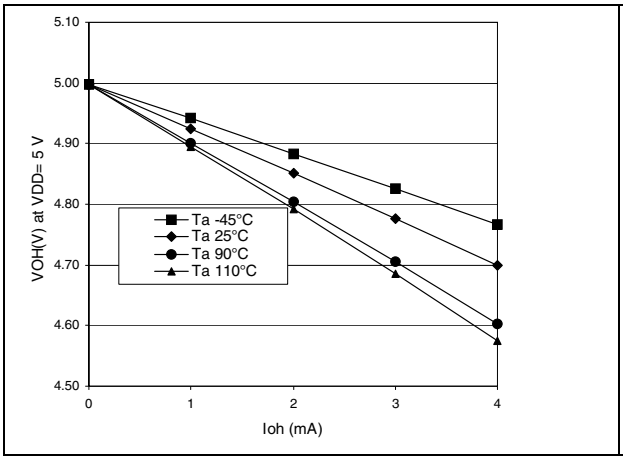


Figure 14. V_{OL} standard ports vs I_{OL} @ V_{DD} 5 V

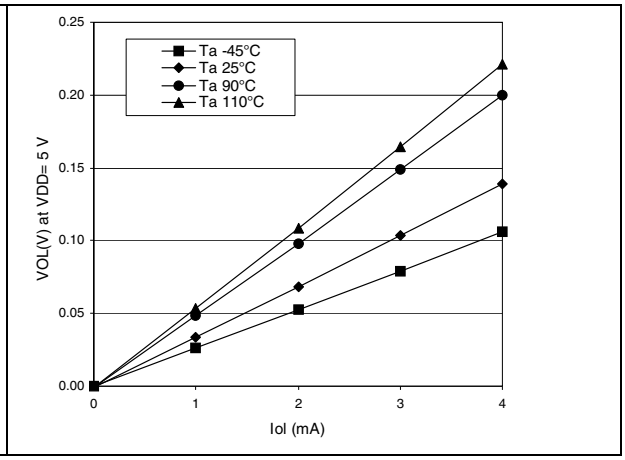


Figure 15. V_{OH} JTDO pin vs I_{OL} @ V_{DD} 5 V

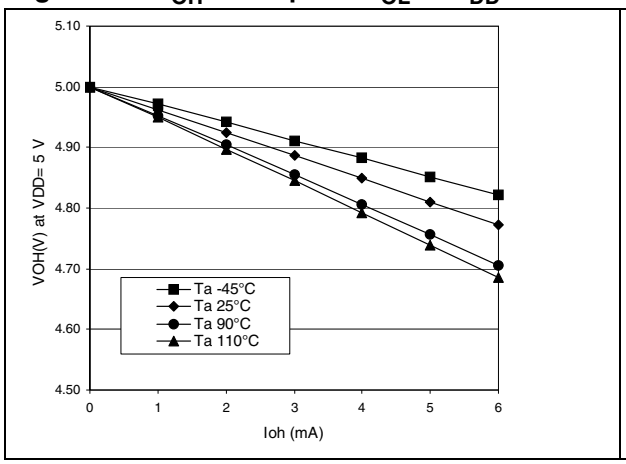


Figure 16. V_{OL} JTDO pin vs I_{OL} @ V_{DD} 5 V

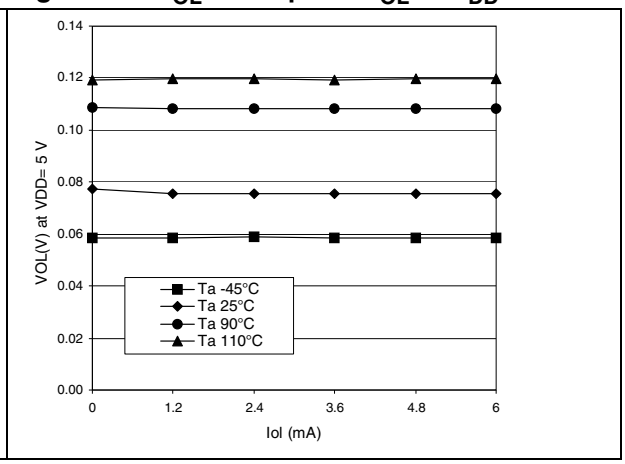


Figure 17. V_{OH} P6.0 pin vs I_{OL} @ V_{DD} 5 V

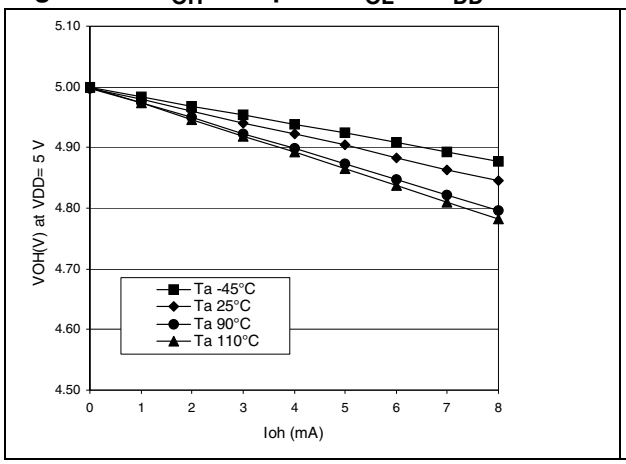
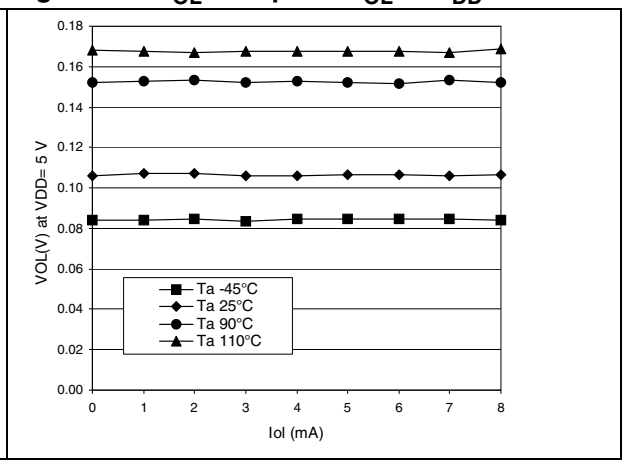


Figure 18. V_{OL} P6.0 pin vs I_{OL} @ V_{DD} 5 V



5.2 Thermal characteristics

The average chip-junction temperature, T_J, in degrees Celsius, may be calculated using the following equation:

$$T_J = T_A + (P_D \times \Theta_{JA}) \quad (1)$$

Where:

- T_A is the ambient temperature in °C,
- Θ_{JA} is the package junction-to-ambient thermal resistance, in °C/W,
- P_D is the sum of P_{INT} and $P_{I/O}$ ($P_D = P_{INT} + P_{I/O}$),
- P_{INT} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the chip internal power,
- $P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant if the device is configured to drive continuously external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

$$P_D = K / (T_J + 273°C) \quad (2)$$

Therefore (solving equations 1 and 2):

$$K = P_D \times (T_A + 273°C) + \Theta_{JA} \times P_D^2 \quad (3)$$

Where:

- K is a constant for the particular part, which may be determined from equation (3) by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J may be obtained by solving equations (1) and (2) iteratively for any value of T_A

Table 28. Thermal characteristics

Symbol	Description	Package	Value (typical)	Unit
Θ_{JA}	Thermal resistance junction-ambient	LFBGA144	50	°C/W
		TQFP144	40	
		TQFP100	40	

7 Known limitations

7.1 Low power wait for interrupt mode

When the STR73x device is put in Low Power Wait For Interrupt mode (LPWFI), the Flash goes into low power mode or power down mode, depending on the setting of the PWD bit in the Flash Control Register 0 (default is '0', Low Power mode). This default mode can create excessive voltage conditions on the transistor gates and may affect the long term behavior of the Low Power mode circuitry.

Workaround

There is no workaround. If Low Power Wait For Interrupt mode is used, it is strongly suggested to configure the Flash to enter power down mode (bit PWD = '1').

7.2 PLL free running mode at high temperature

When the STR73x device is operated and an ambient temperature (T_A) of more than 55° C and the main system clock (f_{MCLK}) is sourced by the PLL in free running mode, the device may not work properly.

Workaround

At high temperature (more than 55° C), it is recommended to use the internal RC oscillator as a backup clock source rather than the PLL free running mode.